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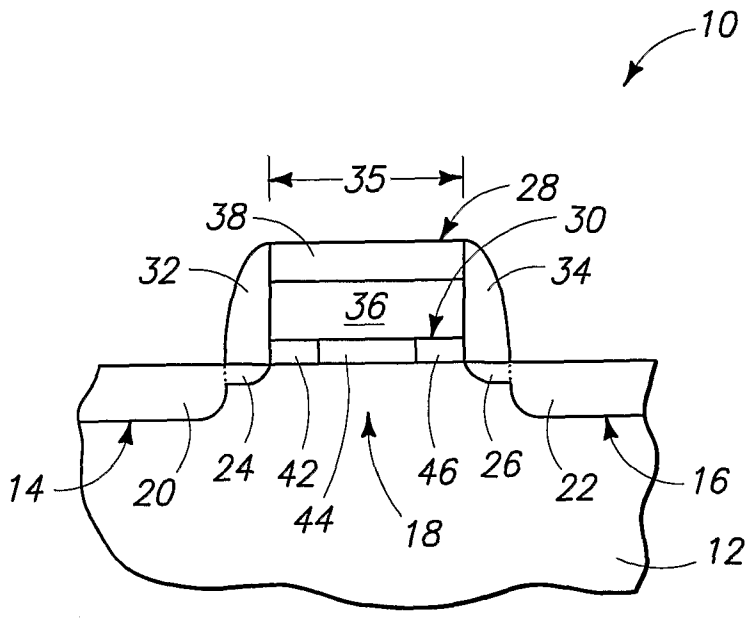
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(54) Title: GATED FIELD EFFECT DEVICES AND METHODS OF FORMING A GATED FIELD EFFECT DEVICE



(57) Abstract: This invention includes gated field effect devices, and methods of forming gated field effect devices. In one implementation, a gated field effect device includes a pair of source/drain regions having a channel region therebetween. A gate is received proximate the channel region between the source/drain regions. The gate has a gate width between the source/drain regions. A gate dielectric is received intermediate the channel region and the gate. The gate dielectric has at least two different regions along the width of the gate. The different regions are characterized by different materials which are effective to define the two different regions to have different dielectric constants k. Other aspects and implementations are contemplated.

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